

Description

The NCE1520 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

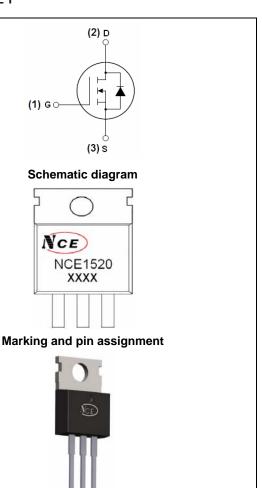
- V_{DS} = 150V, I_{D} =20A $R_{DS(ON)}$ <85mΩ @ V_{GS} =10V (Typ:70mΩ)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Boost converters
- LED backlighting
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



TO-220-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE1520	NCE1520	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	150	V
V _G s	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	20	А
I _D (100℃)	Drain Current-Continuous(TC=100℃)	14	Α
I _{DM}	Pulsed Drain Current	40	Α
P _D	Maximum Power Dissipation	75	W
	Derating factor	0.5	W/℃
E _{AS}	Single pulse avalanche energy (Note 5)	200	mJ
T_{J}, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 175	$^{\circ}$



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NCE1520

Thermal Characteristic

R _{0JC} Thermal Resistance, Junc	on-to-Case (Note 2)	2.0 °C/W	
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Electrical Characteristics (T_C=25 °C unless otherwise noted)

S	ymbol Parameter	Condition	Min	Тур	Max	Unit
Off Characteristic	s					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =250μA	150	165	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =150V,V _{GS} =0V	-	-	1	μΑ
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristic	s ^(Note 3)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2	3.4	4	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =10A	-	70	85	mΩ
g FS	Forward Transconductance	V _{DS} =5V,I _D =10A		20	-	S
Dynamic Characte	eristics (Note4)					
C _{lss}	Input Capacitance)/ OF)/)/ O)/	-	2000	-	PF
C _{oss}	Output Capacitance	$V_{DS}=25V,V_{GS}=0V,$ F=1.0MHz	-	290	-	PF
C _{rss}	Reverse Transfer Capacitance	F=1.UIVITZ	-	180	-	PF
Switching Charac	teristics (Note 4)					
t _{d(on)}	Turn-on Delay Time		-	10.5	-	nS
t _r	Turn-on Rise Time	V_{DD} =75 V , R_L =5 Ω	-	5.5	-	nS
t _{d(off)}	Turn-Off Delay Time	V_{GS} =10V, R_{GEN} =3 Ω	-	14.5	-	nS
t _f	Turn-Off Fall Time		-	3	-	nS
Qg	Total Gate Charge	\/ -75\/ -104	-	17	-	nC
Q _{gs}	Gate-Source Charge	V_{DS} =75V, I_{D} =10A, V_{GS} =10V	-	4	-	nC
Q _{gd}	Gate-Drain Charge	V _{GS} -10V	-	4.4	-	nC
Drain-Source Dio	de Characteristics					
V _{SD}	Diode Forward Voltage (Note 3)	V _{GS} =0V,I _S =20A	-	-	1.2	V
Is	Diode Forward Current (Note 2)	-	-	-	20	Α
t _{rr}	Reverse Recovery Time	TJ = 25°C, IF = 10A	-	32	-	nS
Qrr	Reverse Recovery Charge	di/dt = 100A/μs ^(Note3)	-	53	-	nC
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+				y LS+LD)

Notes:

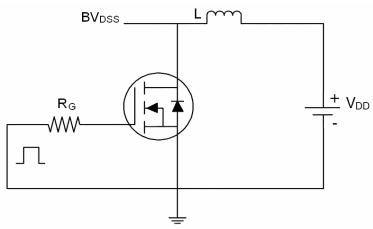
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition:Tj=25 $^{\circ}\text{C}$,VDD=50V,VG=10V,L=0.5mH,Rg=25 Ω

Pb Free Product

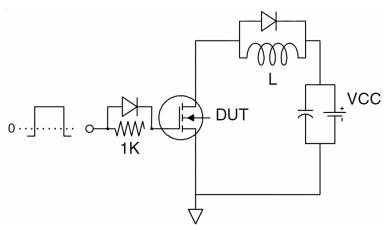


Test Circuit

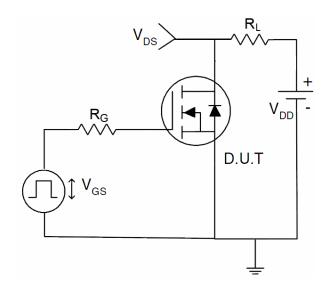
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

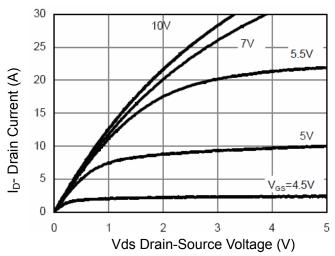


Figure 1 Output Characteristics

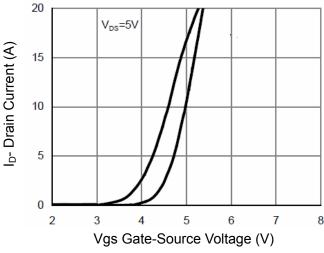


Figure 2 Transfer Characteristics

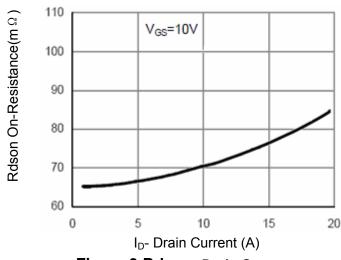


Figure 3 Rdson- Drain Current

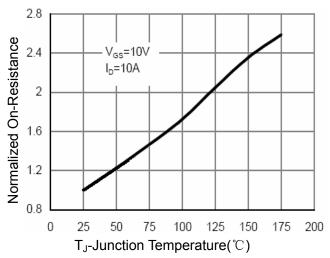


Figure 4 Rdson-JunctionTemperature

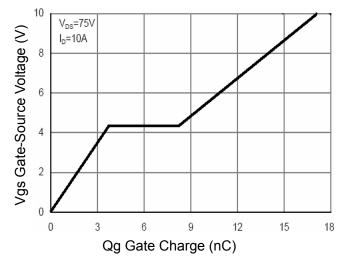


Figure 5 Gate Charge

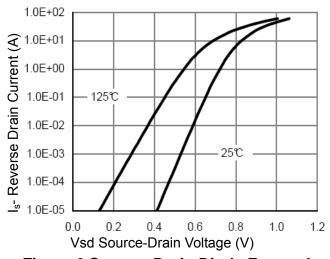


Figure 6 Source- Drain Diode Forward



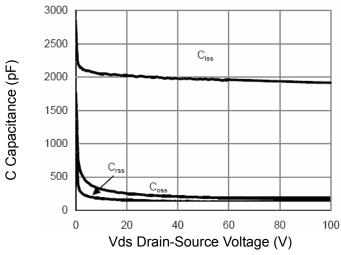
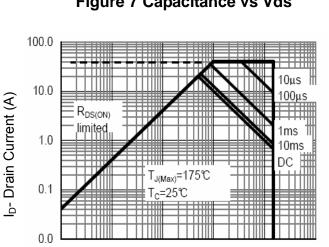


Figure 7 Capacitance vs Vds



Vds Drain-Source Voltage (V) Figure 8 Safe Operation Area

10

100

1000

0.01

0.1

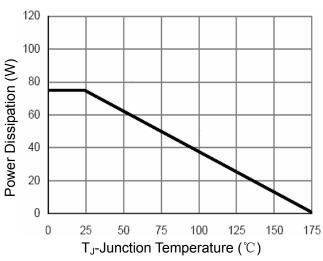


Figure 9 Power De-rating

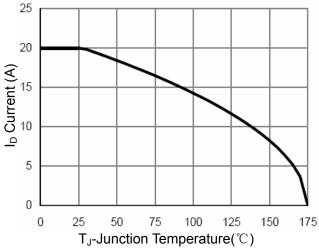


Figure 10ID Current- Junction Temperature

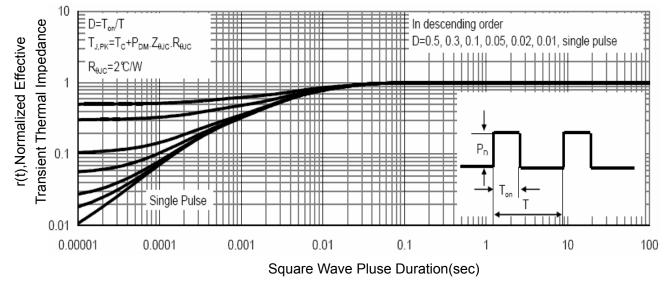
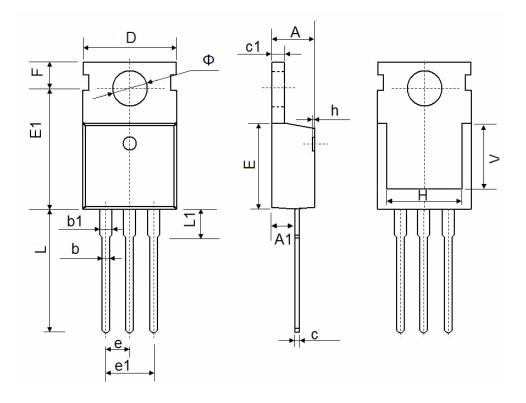


Figure 11 Normalized Maximum Transient Thermal Impedance

Pb Free Product



TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
Е	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	2.540 TYP.		TYP.	
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Φ	3.400	3.800	0.134	0.150	



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